

Abstract

A method is described for producing a semiconductor component (100; ...; 2200) particularly a multilayer semiconductor element, preferably a micromechanical component, particularly a pressure sensor, having a semiconductor substrate (101), particularly made of silicon, and a semiconductor component produced according to the method.

In particular in order to reduce the production cost of such a semiconductor component, it is suggested that the method be refined so that in a first step a first porous layer (104; 1001; 1301) is produced in the semiconductor component, and in a second step a hollow or cavity (201; 1101; 1201; 1401; 2101; 2201) is produced under or from the first porous layer (104; 1001; 1301) in the semiconductor component, with the hollow or cavity capable of being provided with an external access opening.

(Figure 1)